

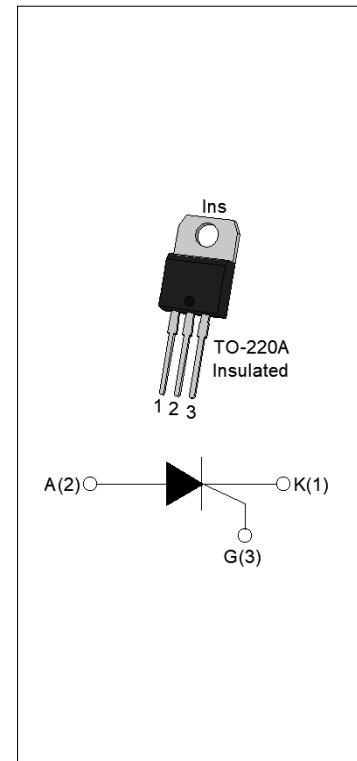


DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT620AH SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT620AH provides a rated insulation voltage of 2500 V_{RMS} , complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	20	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	≤ 15	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-150	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	600	V
Average on-state current ($T_c \leq 123^{\circ}C$)	$I_{T(AV)}$	13	A
RMS on-state current ($T_c \leq 123^{\circ}C$)	$I_{T(RMS)}$	20	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^{\circ}C$)	I_{TSM}	250	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^{\circ}C$)		275	
I^2t value for fusing ($t_p=10ms, T_j=25^{\circ}C$)	I^2t	312.5	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=150^{\circ}C$)	di/dt	150	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=150^{\circ}C$)	I_{GM}	5	A

Average gate power dissipation ($T_j=150^{\circ}\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM} T_j=150^{\circ}\text{C } R_L=3.3\text{k}\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	60	mA
I_H	$I_T=500\text{mA}$	-	-	50	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$	500	-	-	V/ μs
	$V_D=400\text{V}$ Gate Open $T_j=150^{\circ}\text{C}$	300	-	-	
t_{on}	$I_G=40\text{mA } I_A=400\text{mA } I_R=40\text{mA}$ $T_j=25^{\circ}\text{C}$	-	5	-	μs
t_{off}		-	70	-	

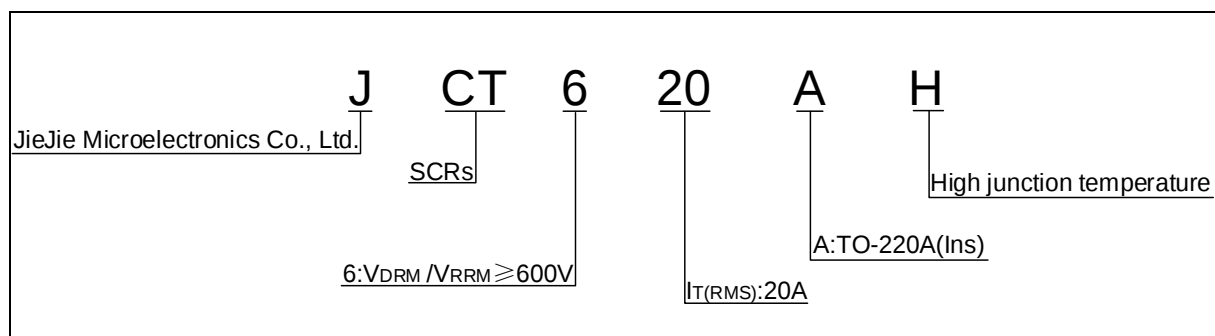
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=40\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.55	V
V_{TO}	Threshold voltage	$T_j=150^{\circ}\text{C}$	0.72	V
R_D	Dynamic resistance	$T_j=150^{\circ}\text{C}$	20	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=150^{\circ}\text{C}$	3	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	1	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient (DC)	60	$^{\circ}\text{C/W}$

ORDERING INFORMATION



MARKING

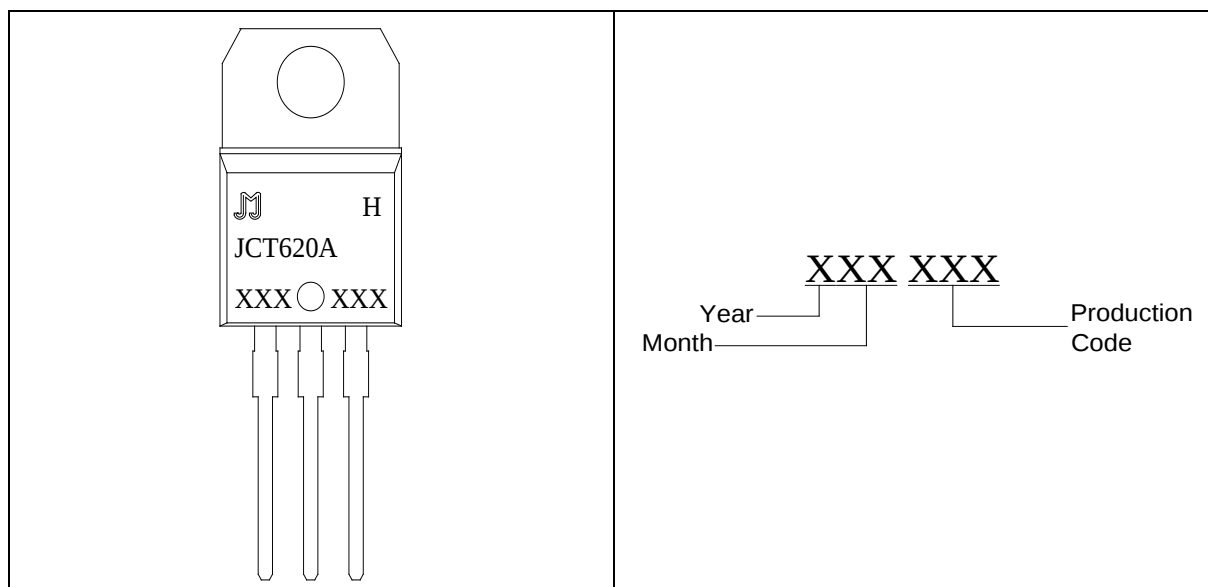


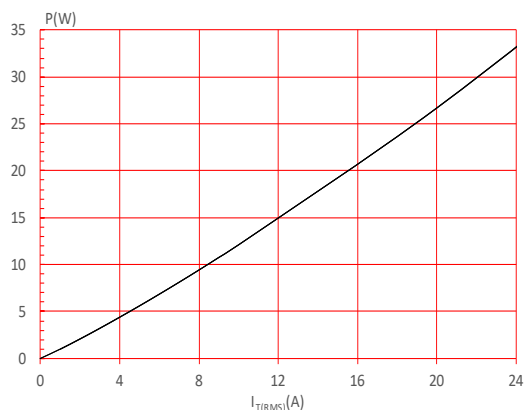
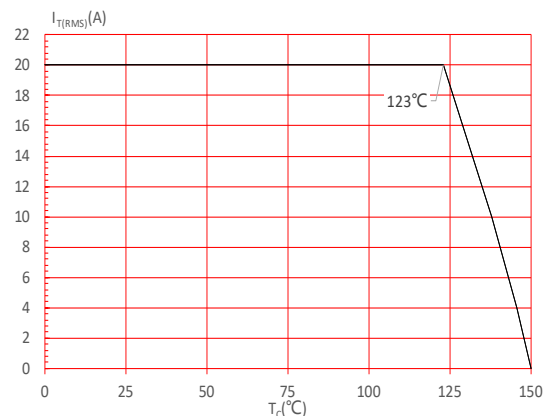
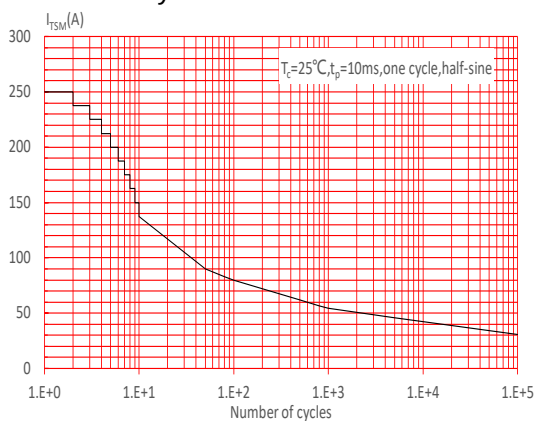
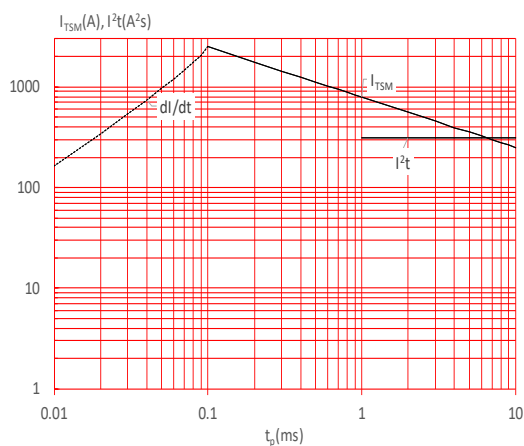
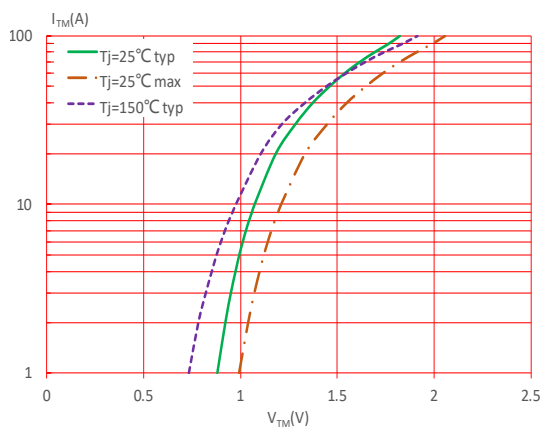
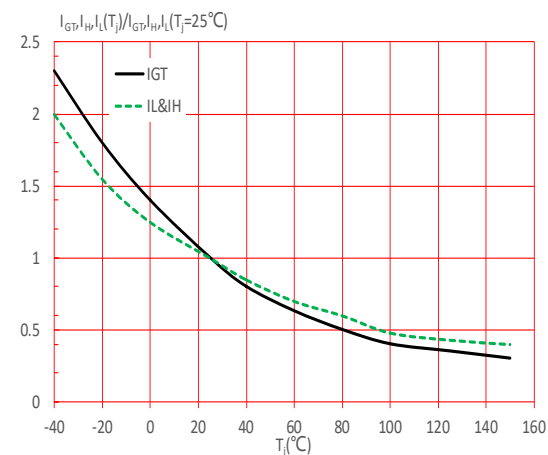
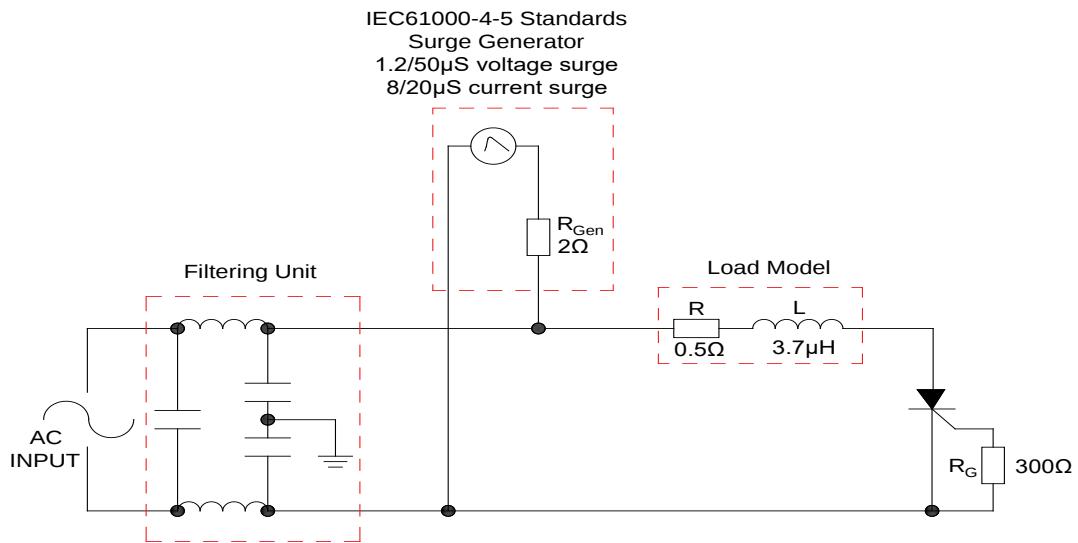
FIG.1: Maximum power dissipation versus RMS on-state current**FIG.2:** RMS on-state current versus case temperature**FIG.3:** Surge peak on-state current versus number of cycles**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of I^2t ($di/dt < 150A/\mu s$)**FIG.4:** On-state characteristics**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

ORDERING INFORMATION

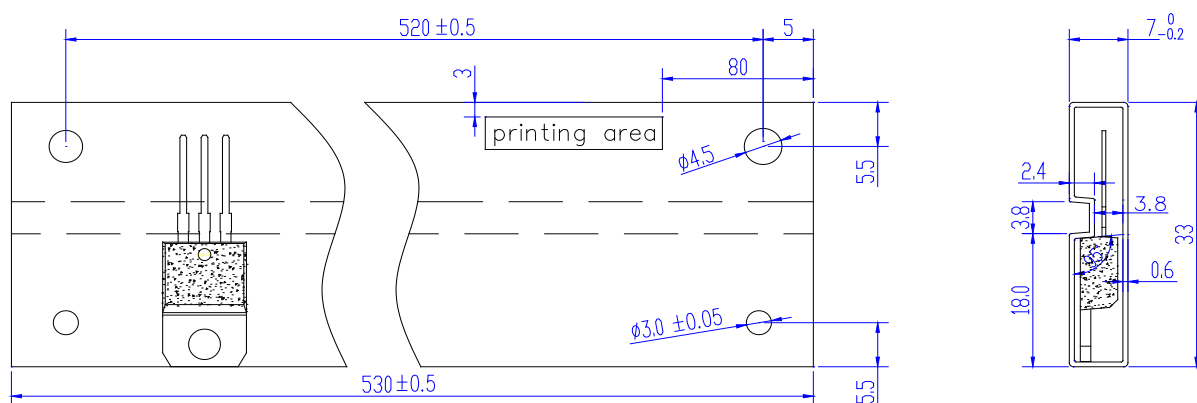
Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT620AH	600	15	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Jun.9, 2023	A.1.0	Last update
Oct.11, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

Technical drawing of a 4-pin connector. The drawing includes a top view, a front view, and a side view. Dimensions are indicated by blue lines and labels: E (total width), I (width of the top section), L3 (height of the top section), L2 (height of the middle section), J (height of the bottom section), K (height of the base), B (width of the base), G (width of the base), H1 (height of the base), E1 (width of the base), A (width of the top section), C2 (width of the top section), C3 (width of the top section), C (width of the top section), D (width of the top section), F (width of the top section). A hole diameter is specified as $\Phi 3.7-3.9\text{mm}$.

DELIVERY MODE



TEL: +86-513-68528666

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.
Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.